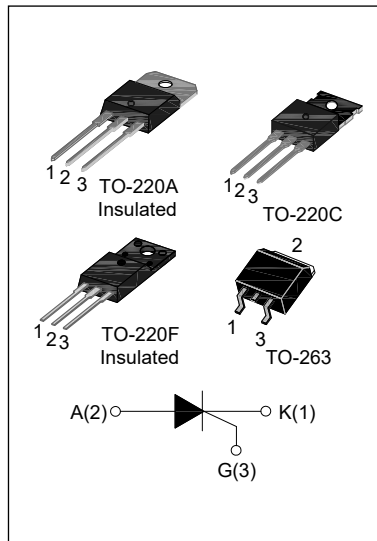




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT630/830 SCRs provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

From all three terminals to external heatsink, JCTx30A provides a rated insulation voltage of 2500 V_{RMS}, and JCTx30F provides a rated insulation voltage of 2000 V_{RMS}, complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	JCT630	JCT830
V _{DRM} / V _{RRM}	600V	800V
I _{T(RMS)}	30A	
I _{GT}	≤15mA	

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range	T _{stg}	-40-150	°C	
Operating junction temperature range	T _j	-40-125	°C	
Repetitive peak off-state voltage(T _j =25°C)	V _{DRM}	600/800	V	
Repetitive peak reverse voltage(T _j =25°C)	V _{RRM}	600/800	V	
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V	
Non repetitive peak reverse voltage	V _{RSM}	V _{RRM} +100	V	
RMS on-state current	TO-220A(Ins) (T _c =97°C)	I _{T(RMS)}	30	A
	TO-220C (T _c =103°C)			
	TO-220F(Ins) /TO-263(T _c =95°C)			

Non repetitive surge peak on-state current (tp=10ms)	I_{TSM}	330	A
I^2t value for fusing (tp=10ms)	I^2t	550	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	50	$A/\mu s$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	-	15	mA
V_{GT}		-	-	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C R_L=3.3K\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	50	mA
I_H	$I_T=500mA$	-	-	40	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$	200	-	-	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=55A$ tp=380 μs	$T_j=25^\circ C$	1.55	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	10	μA
I_{RRM}		$T_j=125^\circ C$	4	mA

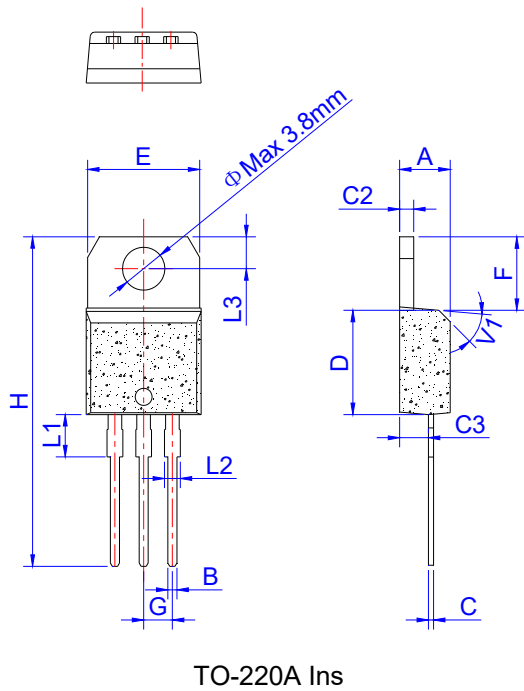
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	1.7	$^\circ C/W$
		TO-220C	0.9	
		TO-220F(Ins)/ TO-263	1.8	

ORDERING INFORMATION

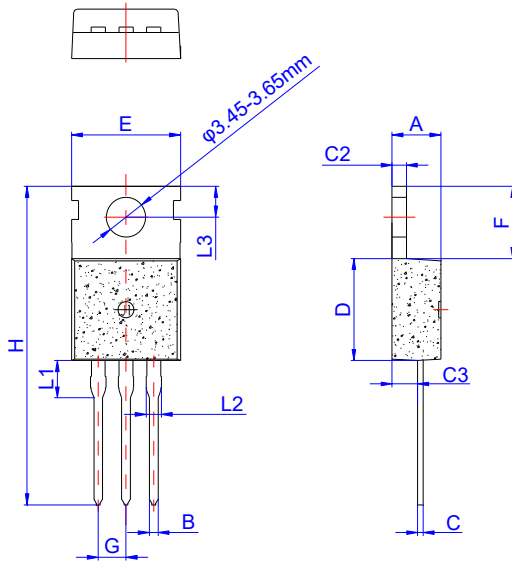
<p>J</p> <p>JieJie Microelectronics Co.,Ltd</p>	<p>CT</p> <p>SCRs</p> <p>6:VDRM /VRRM ≥600V 8:VDRM /VRRM ≥800V</p>	<p>6</p>	<p>30</p> <p>IT(RMS):30A</p>	<p>A</p> <p>E:TO-263 A:TO-220A(Ins) F:TO-220F(Ins) C:TO-220C</p>
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PACKAGE MECHANICAL DATA



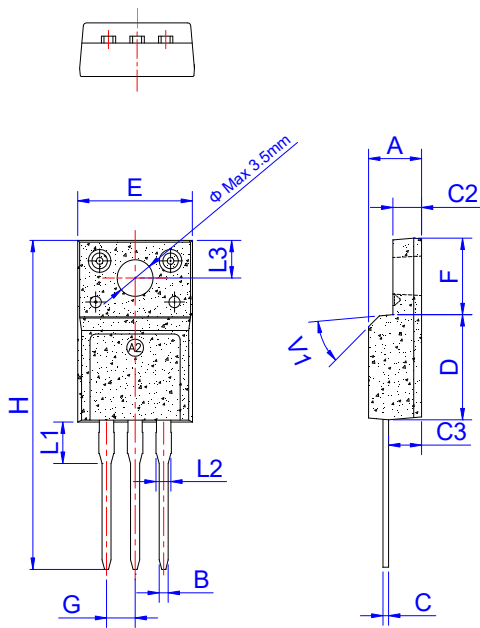
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220C

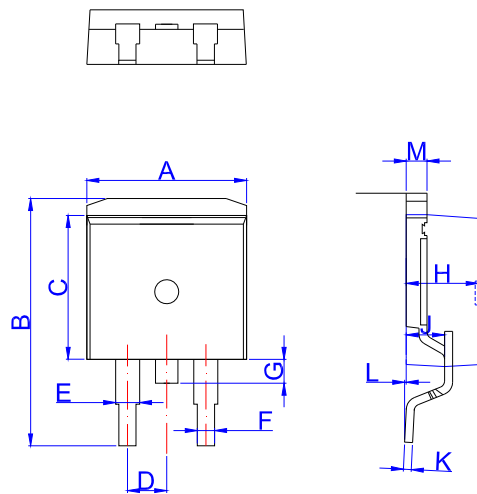
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FIG.1: Maximum power dissipation versus RMS on-state current

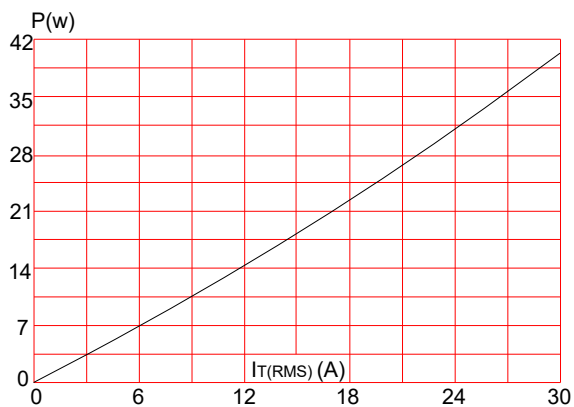


FIG.2: RMS on-state current versus case temperature

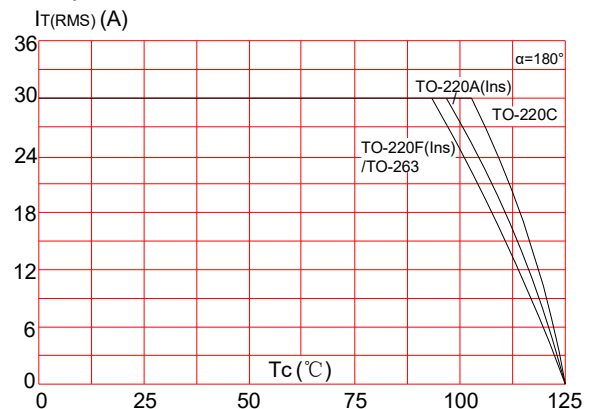


FIG.3: Surge peak on-state current versus number of cycles

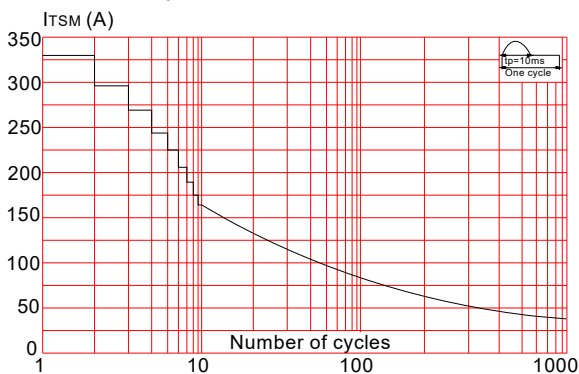


FIG.4: On-state characteristics (maximum values)

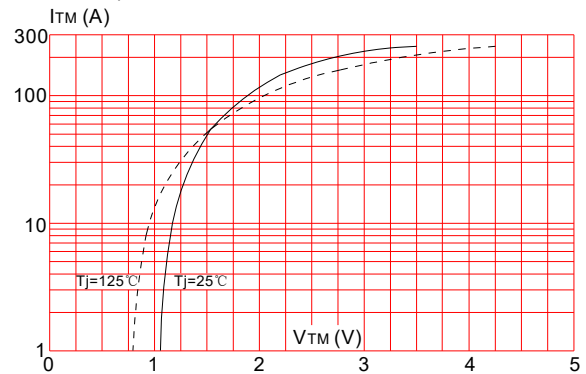


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

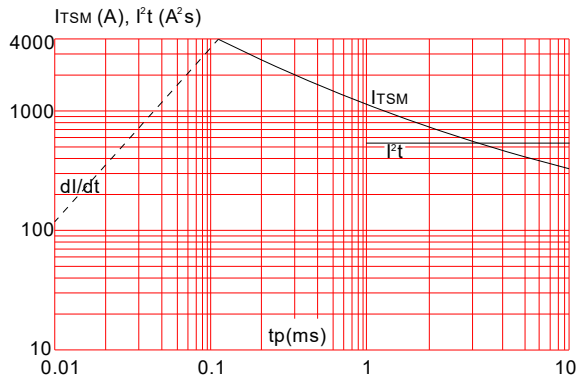
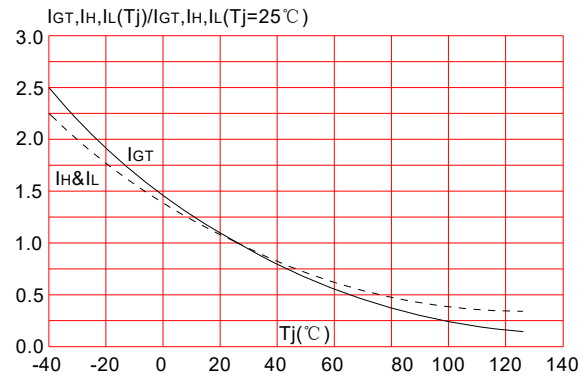



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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